

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE

2SA1811

LOW FREQUENCY AMPLIFIER APPLICATIONS.

DRIVER STAGE AMPLIFIER APPLICATIONS.

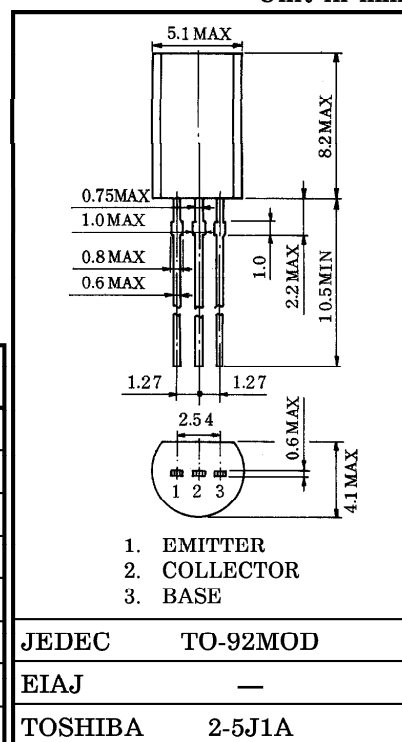
SWITCHING APPLICATIONS.

Unit in mm

- Excellent h_{FE} Linearity
: $h_{FE(2)} = 35$ (Min.), ($V_{CE} = -2V$, $I_C = -300mA$)
- Complementary to 2SC4707

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Base Current	I_B	-100	mA
Collector Power Dissipation	P_C	800	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



Weight : 0.36g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -35V$, $I_E = 0$	—	—	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V$, $I_C = 0$	—	—	-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -2V$, $I_C = -100mA$	100	—	300	
	$h_{FE(2)}$	$V_{CE} = -2V$, $I_C = -300mA$	35	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -300mA$, $I_B = -30mA$	—	-0.2	-0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -2V$, $I_C = -100mA$	—	-0.8	-1.0	V
Transition Frequency	f_T	$V_{CE} = -6V$, $I_C = -20mA$	—	200	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -6V$, $I_E = 0$, $f = 1MHz$	—	9	—	pF

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